

Title (en)
Display device and manufacturing method thereof

Title (de)
Anzeigegerät und Herstellungsverfahren dafür

Title (fr)
Dispositif d'affichage et son procédé de fabrication

Publication
EP 1544842 A3 20091118 (EN)

Application
EP 04029476 A 20041213

Priority
JP 2003421599 A 20031218

Abstract (en)
[origin: EP1544842A2] A display device capable of applying reverse driving voltage for a light emitting element to a light emitting element every certain period for prolonging light emitting element's life and burning out a shorted portion. Besides a path for supplying forward current to the light emitting element, a path for supplying reverse current is provided. A driving transistor is provided in the former path while a transistor (AC transistor) is provided in the latter path, thereby a switching between the two paths is controlled. The AC transistor has a rate L/W of a channel length L to a channel width W smaller than that of the driving transistor. Accordingly, current flowing into the light emitting element can be flowed into the AC transistor in the case of reverse driving voltage being applied to the light emitting element.

IPC 8 full level
G09G 3/30 (2006.01); **G09G 3/32** (2006.01); **G09G 3/10** (2006.01); **G09G 3/20** (2006.01); **H05B 33/12** (2006.01); **G09G 5/399** (2006.01); **H01L 27/32** (2006.01)

CPC (source: EP KR US)
G09G 3/20 (2013.01 - KR); **G09G 3/30** (2013.01 - KR); **G09G 3/3233** (2013.01 - EP US); **G09G 3/3266** (2013.01 - EP US); **G09G 3/3291** (2013.01 - EP US); **G09G 3/2022** (2013.01 - EP US); **G09G 5/399** (2013.01 - EP US); **G09G 2300/0417** (2013.01 - EP US); **G09G 2300/0842** (2013.01 - EP US); **G09G 2310/0256** (2013.01 - EP US); **G09G 2320/043** (2013.01 - EP US); **G09G 2360/18** (2013.01 - EP US); **H10K 59/12** (2023.02 - EP KR US); **H10K 59/122** (2023.02 - EP US); **H10K 71/841** (2023.02 - EP US); **H10K 71/861** (2023.02 - EP US); **H10K 2102/3026** (2023.02 - EP US)

Citation (search report)
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Designated contracting state (EPC)
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Designated extension state (EPC)
AL BA HR LV MK YU

DOCDB simple family (publication)
EP 1544842 A2 20050622; EP 1544842 A3 20091118; EP 1544842 B1 20180822; CN 1638559 A 20050713; CN 1638559 B 20101013; KR 101062242 B1 20110905; KR 20050061321 A 20050622; TW 200521915 A 20050701; TW I382379 B 20130111; US 2005134189 A1 20050623; US 7460095 B2 20081202

DOCDB simple family (application)
EP 04029476 A 20041213; CN 200410082150 A 20041217; KR 20040105288 A 20041214; TW 93138763 A 20041214; US 1188104 A 20041214